

Silicon NPN Power Transistors

BU508AFI

DESCRIPTION

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- With TO-3PML package
- High voltage
- High speed switching

APPLICATIONS

- For use in horizontal deflection of colour TV receivers

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

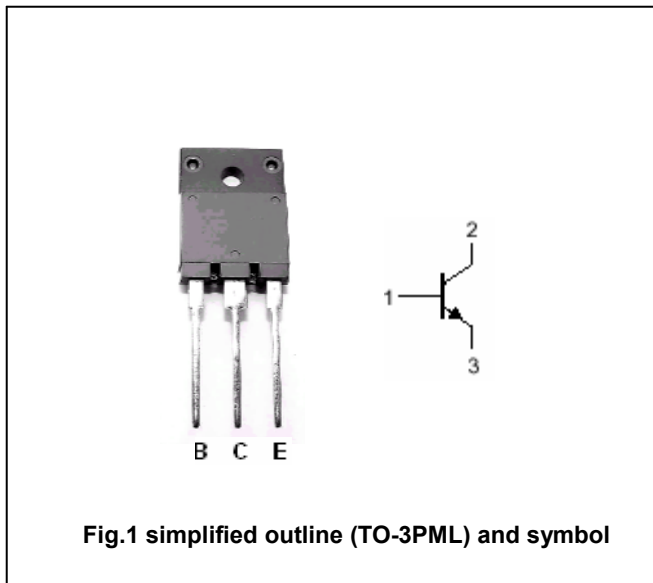


Fig.1 simplified outline (TO-3PML) and symbol

Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	Open emitter	1500	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	700	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	10	V
I <sub>C</sub>	Collector current (DC)		8	A
I <sub>CP</sub>	Collector current (Pulse)		15	A
P <sub>tot</sub>	Total power dissipation	T <sub>C</sub> =25°C	50	W
T <sub>j</sub>	Max.operating junction temperature		150	°C
T <sub>stg</sub>	Storage temperature		-65~150	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R <sub>th j-c</sub>	Thermal resistance junction case	2.5	°C/W

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

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SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-emitter sustaining voltage	I <sub>C</sub> =100mA ; I <sub>B</sub> =0,	700			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =10mA ; I <sub>C</sub> =0	10			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =4.5A ; I <sub>B</sub> =2 A			1.0	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =4.5A ; I <sub>B</sub> =2 A			1.3	V
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =1A; V <sub>CE</sub> =5V	8			
I <sub>CES</sub>	Collector cut-off current	V <sub>CE</sub> =1500V; V <sub>BE</sub> =0 T <sub>C</sub> =125°C			1.0 2.0	mA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =5V; I <sub>C</sub> =0			0.1	mA
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =0.1A; V <sub>CE</sub> =5V; f=5MHz		7		MHz
t <sub>s</sub>	Storage time	I <sub>C</sub> =4.5A ; V <sub>CC</sub> =140V I <sub>B</sub> =1.8A; L <sub>C</sub> =0.9mH		7		μs
t <sub>f</sub>	Fall time	L <sub>B</sub> =3μH		0.55		μs

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PACKAGE OUTLINE

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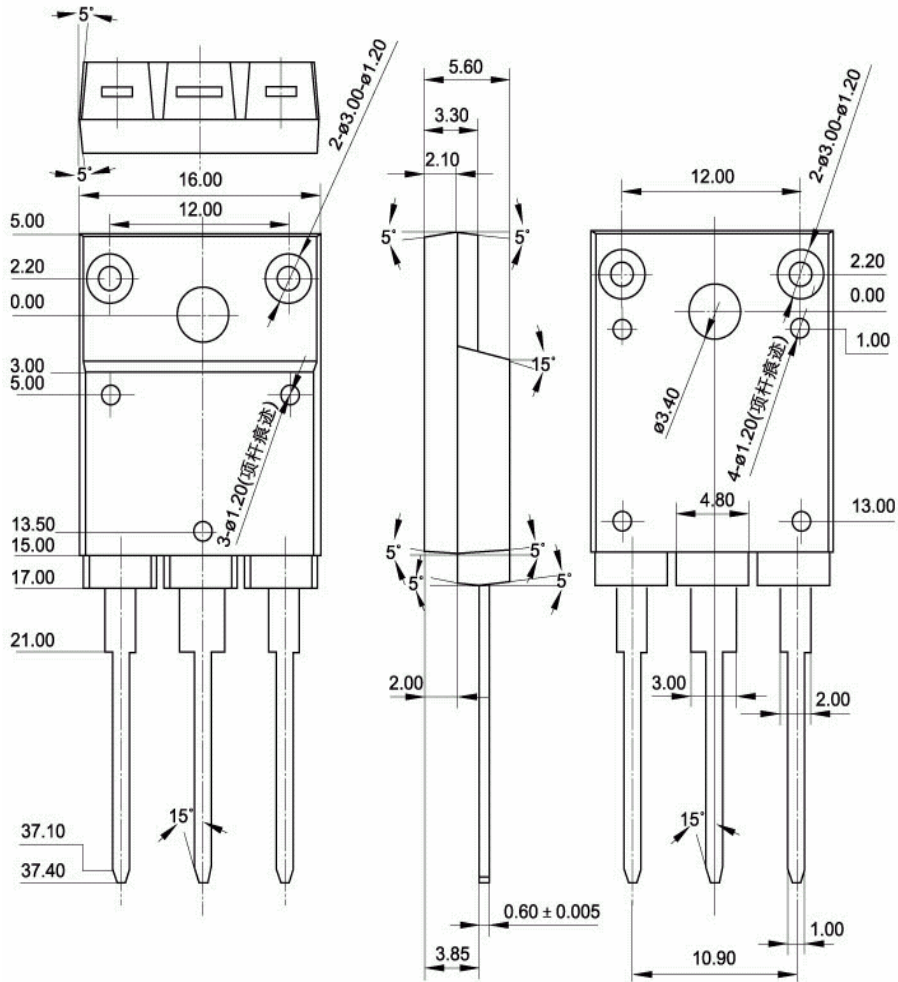


Fig.2 Outline dimensions